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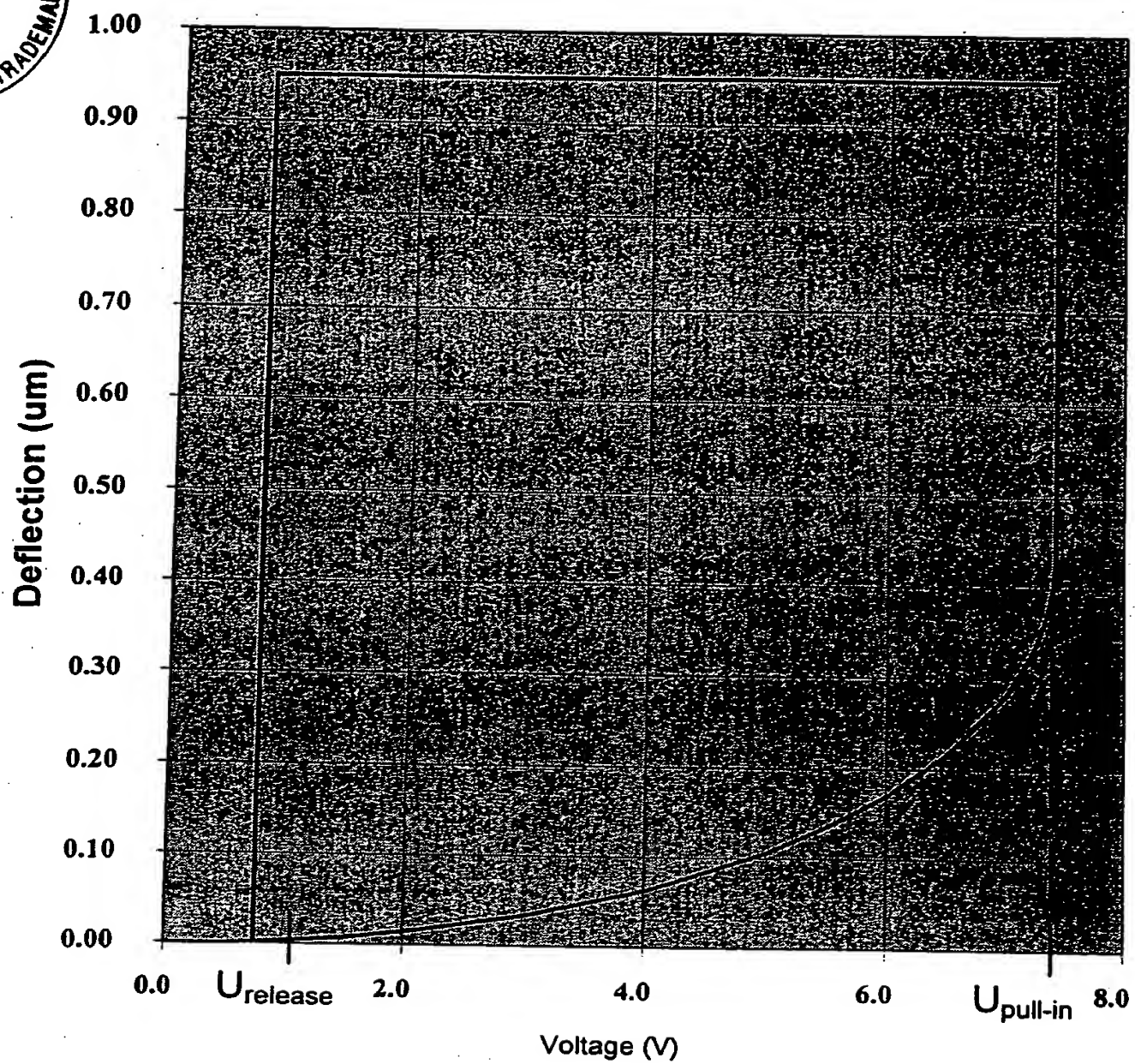
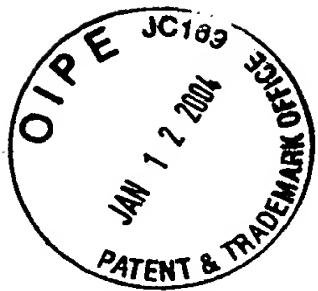


Fig. 1  
PRIOR ART

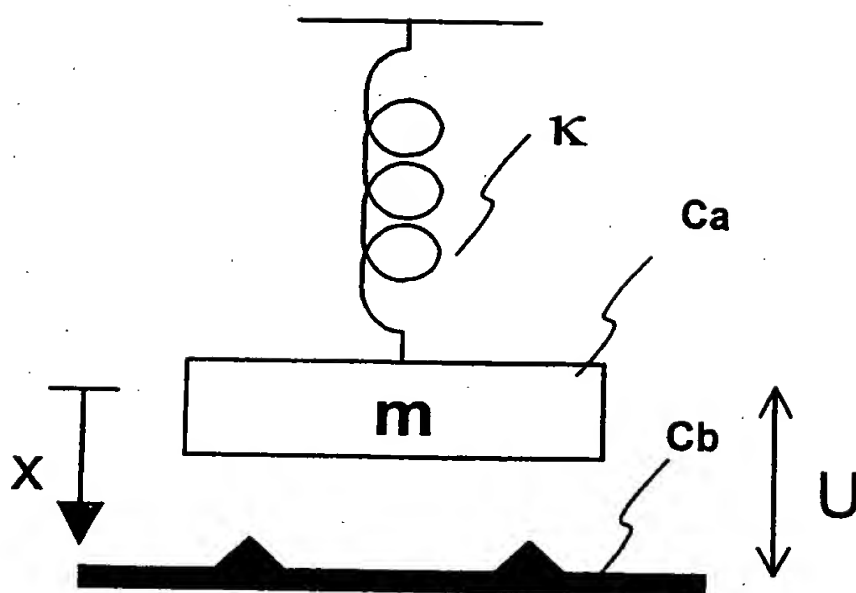
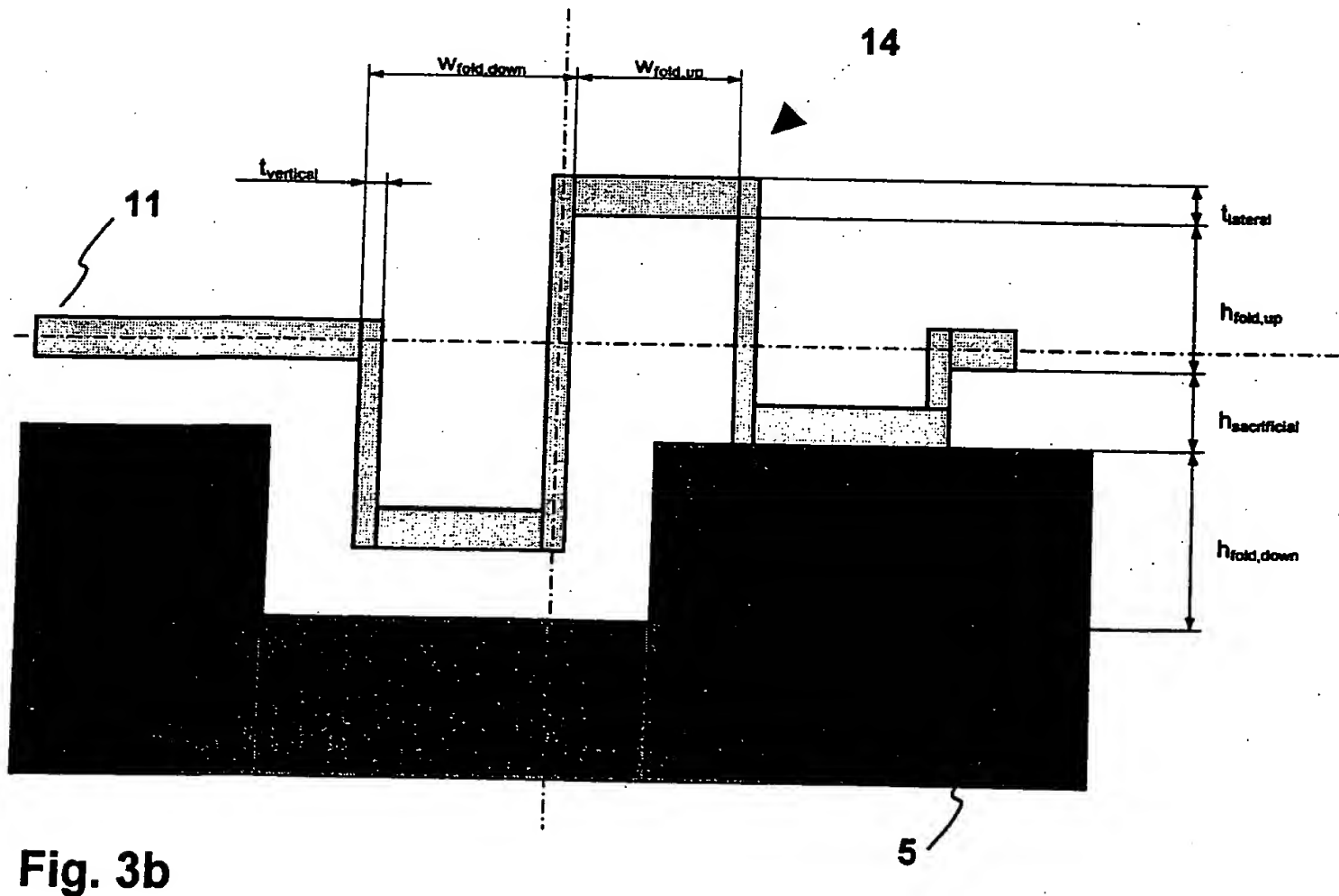
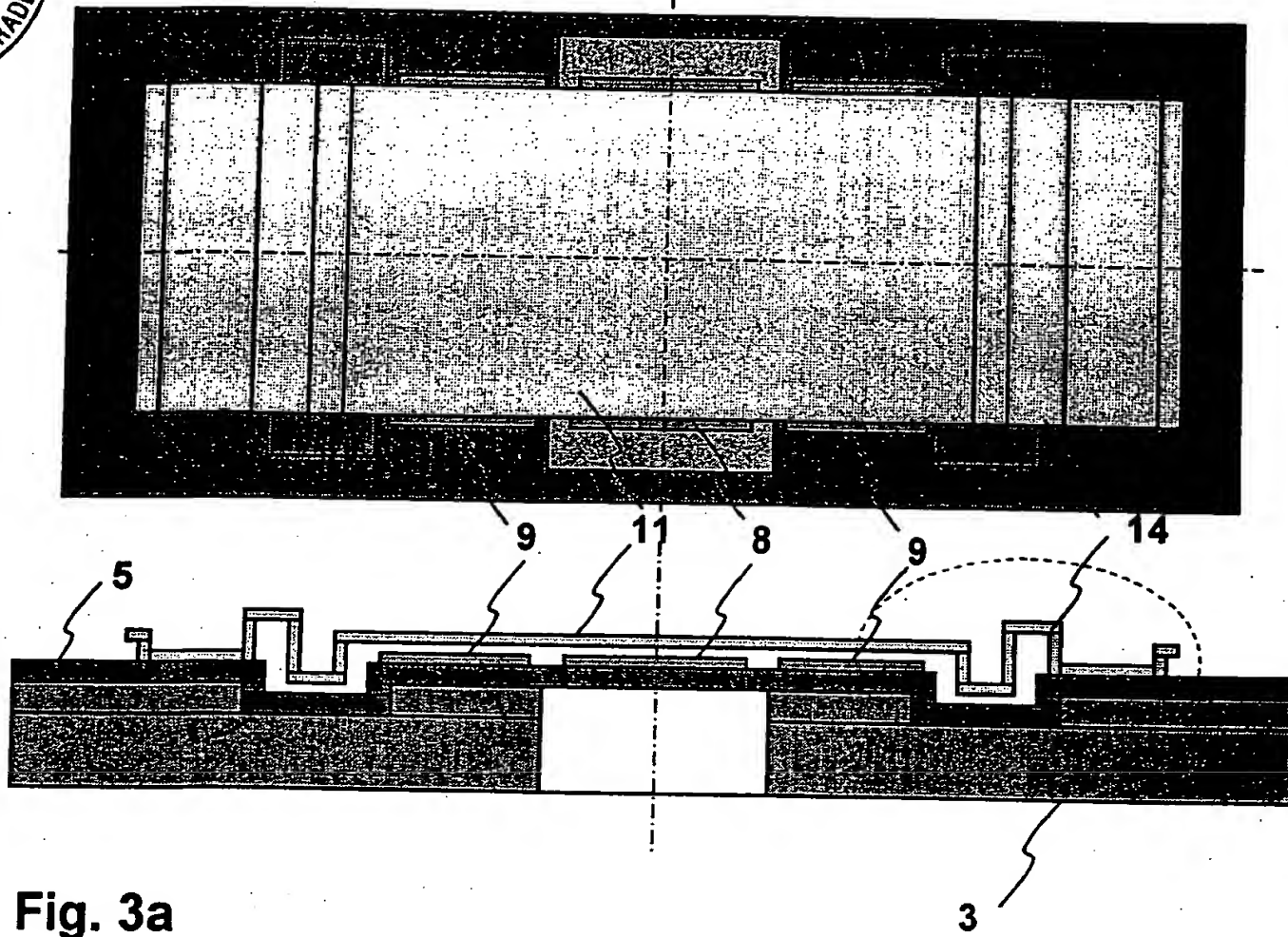
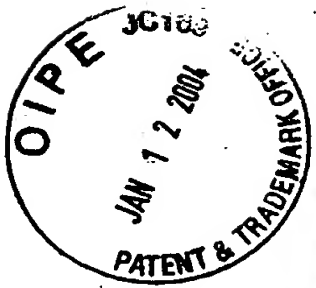
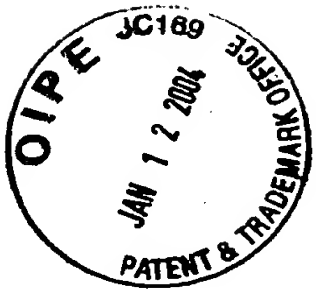


Fig. 2  
PRIOR ART





400

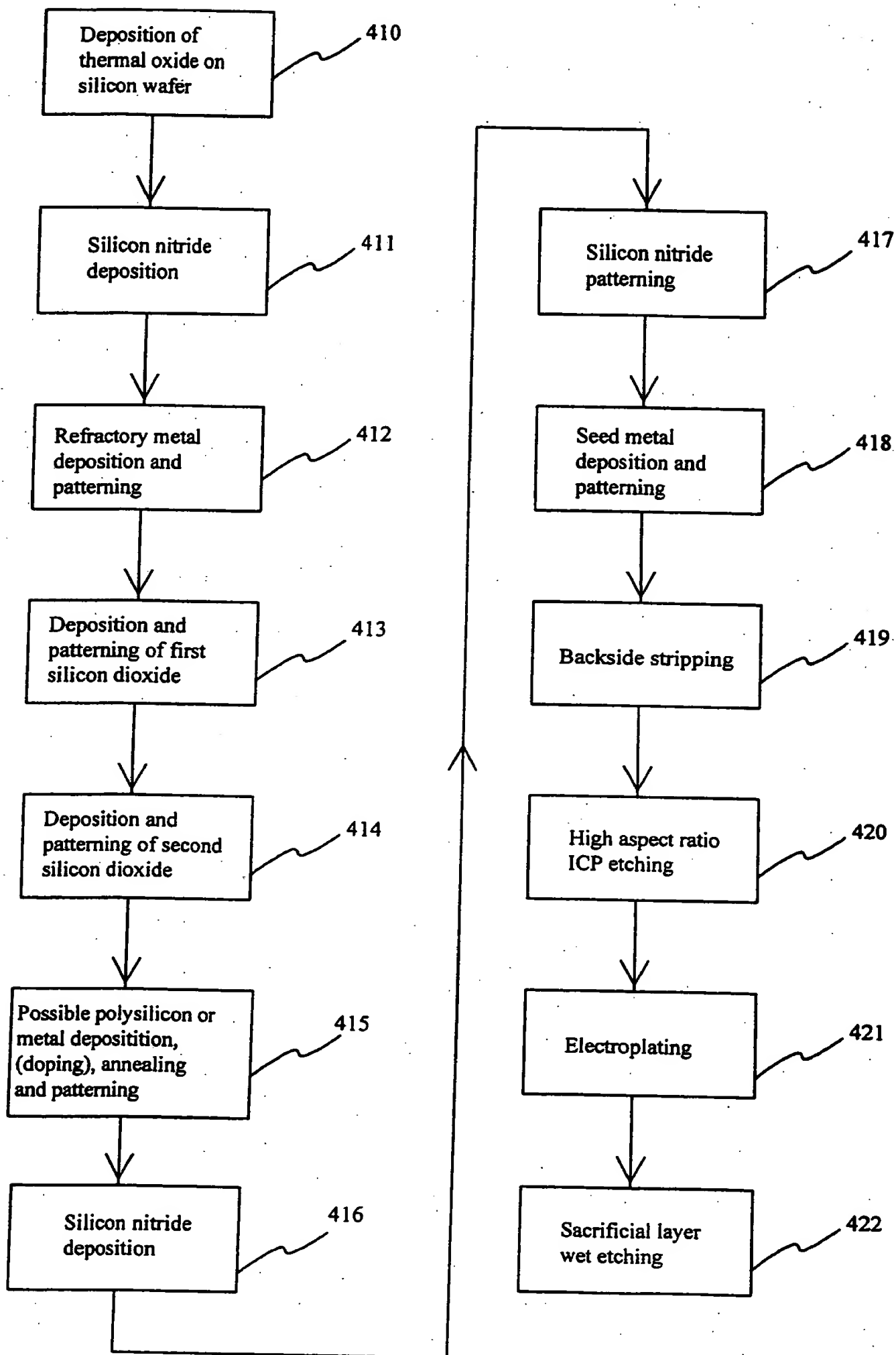
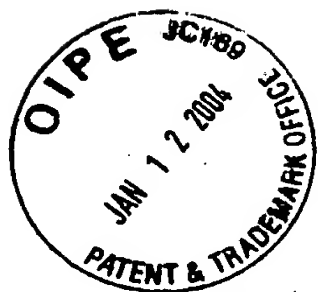
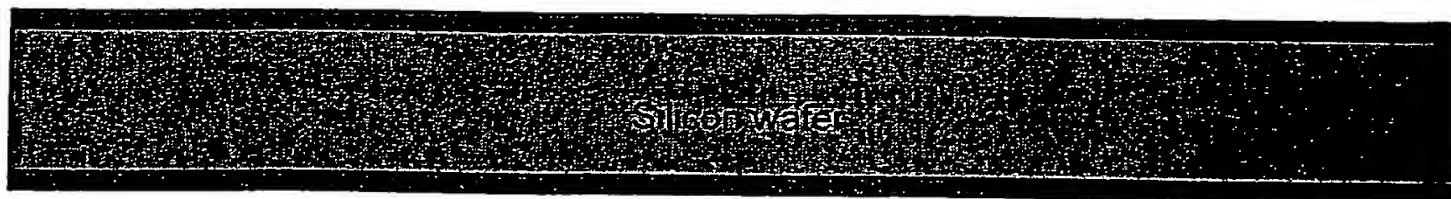


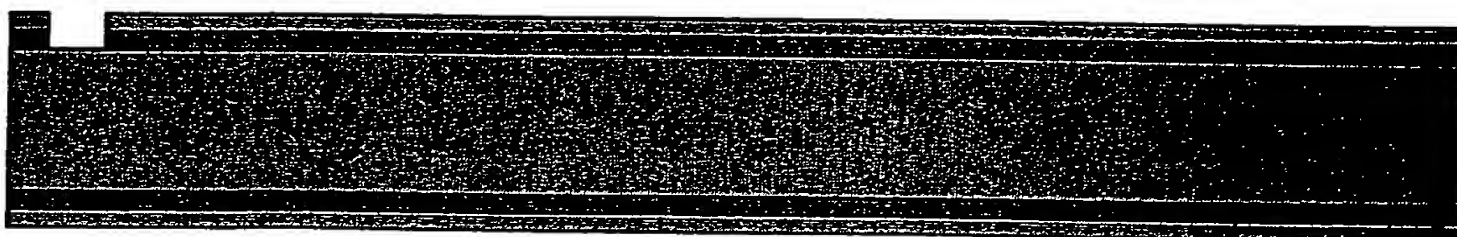
FIG. 4a



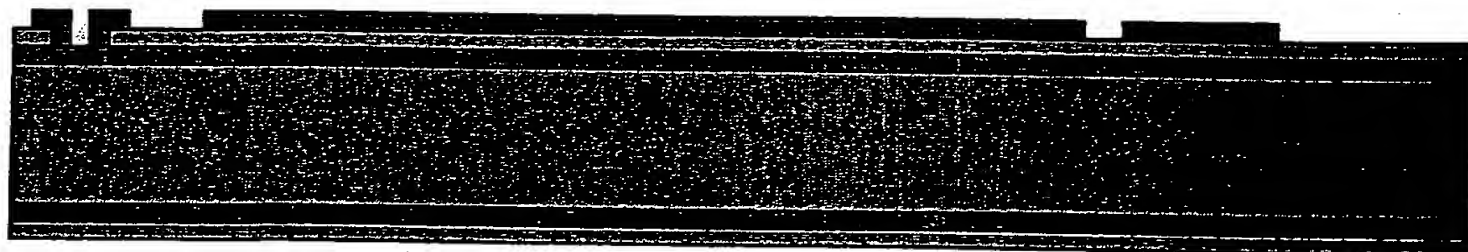
410 Thermal oxide ( $\sim 1\mu\text{m}$ )



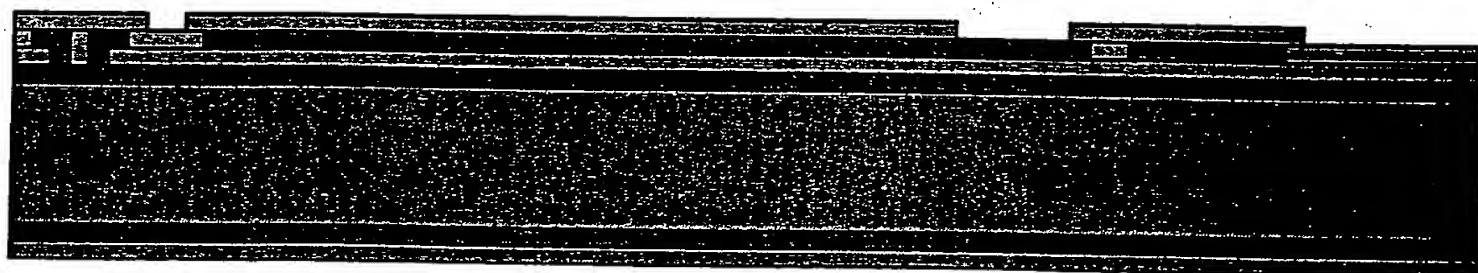
411 Silicon nitride deposition ( $\sim 1\mu\text{m}$ ) and patterning



412 Refractory metal (molybdeen or tungsten) deposition and patterning



413 First silicon dioxide deposition and patterning (plasma) ( $0.4 - 0.5\mu\text{m}$ )



414 Second silicon dioxide deposition and patterning (plasma) ( $0.5\mu\text{m}$ )

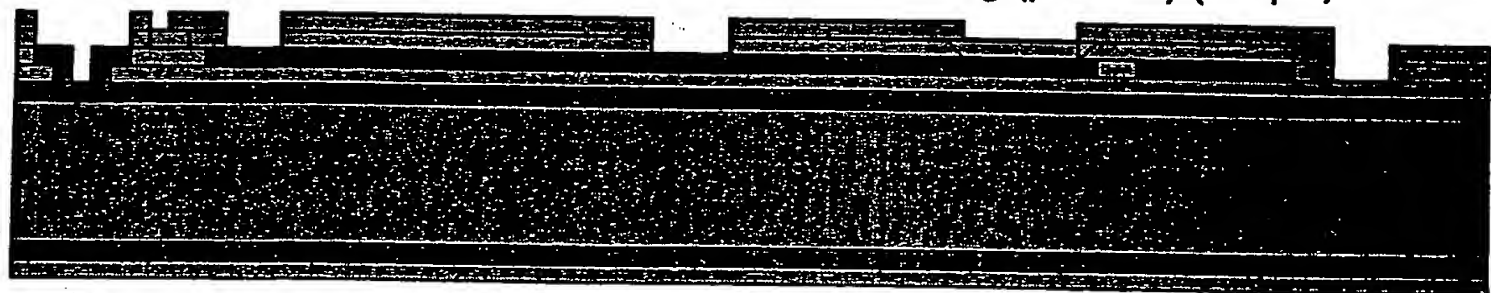
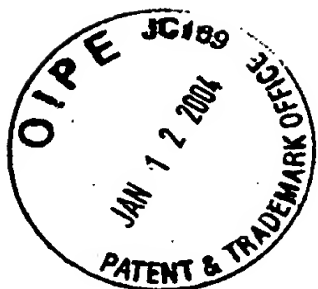


FIG. 4b



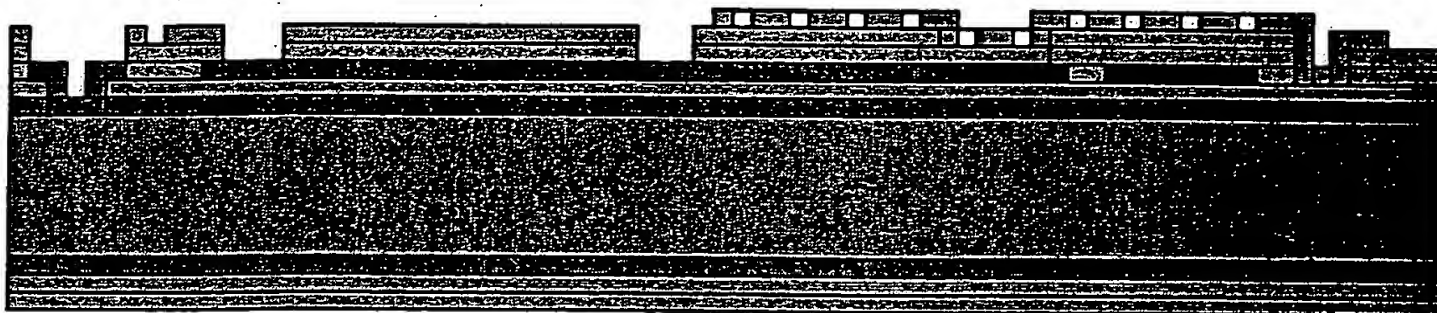
Docket# 297-010113-US (PAR)

S/N 09/783,059

Title: Micromechanical Tunable...

Inventor: Tapani Ryhanen et al. Page # 5 of 17

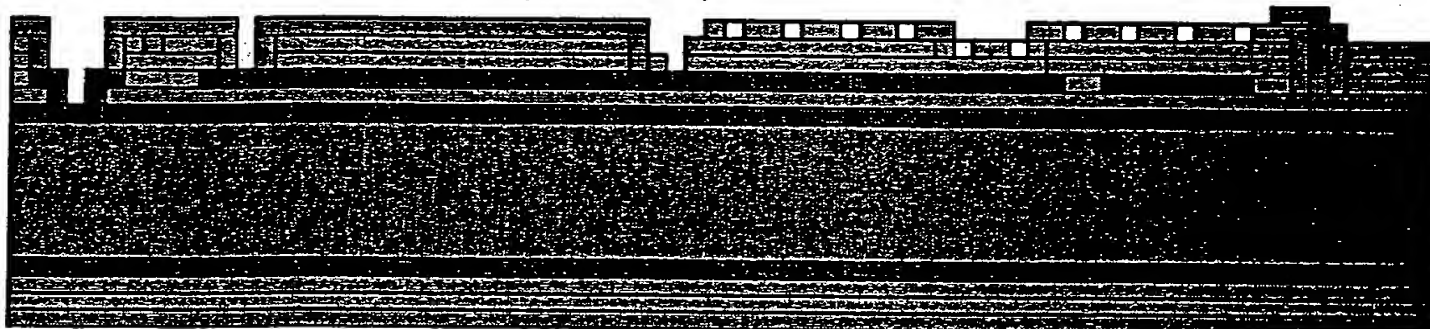
415 Polysilicon deposition (2-5  $\mu\text{m}$ ), doping, annealing and patterning;  
(PolySi:  $< 5 \Omega/\square$ ; tensile residual stress: 10 MPa)



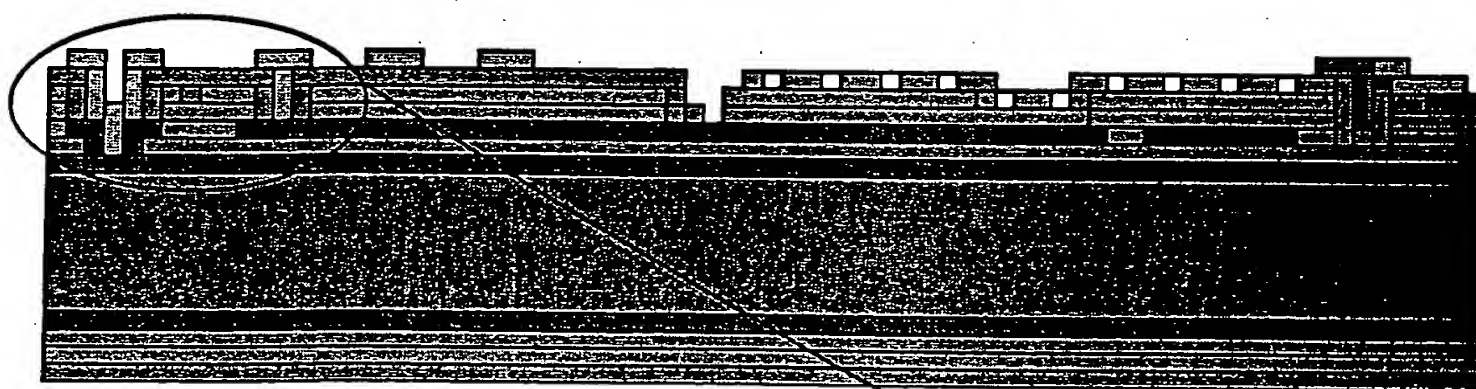
416 Silicon nitride deposition (0.3  $\mu\text{m}$ )



417 Silicon nitride patterning (plasma)



418 Seed metal deposition and patterning



500 nm Au  
300 nm SiN  
800 nm SiO<sub>2</sub>  
500 nm TiW  
1  $\mu\text{m}$  SiN  
1  $\mu\text{m}$  SiO<sub>2</sub>

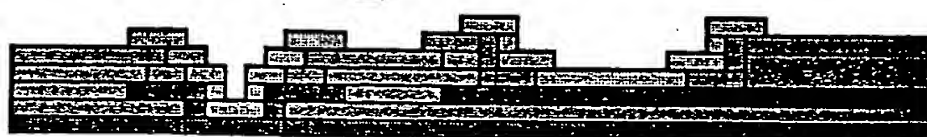
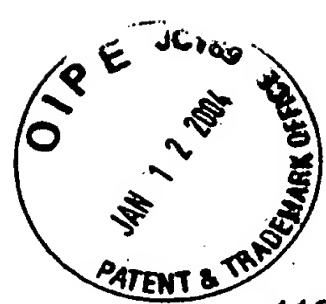
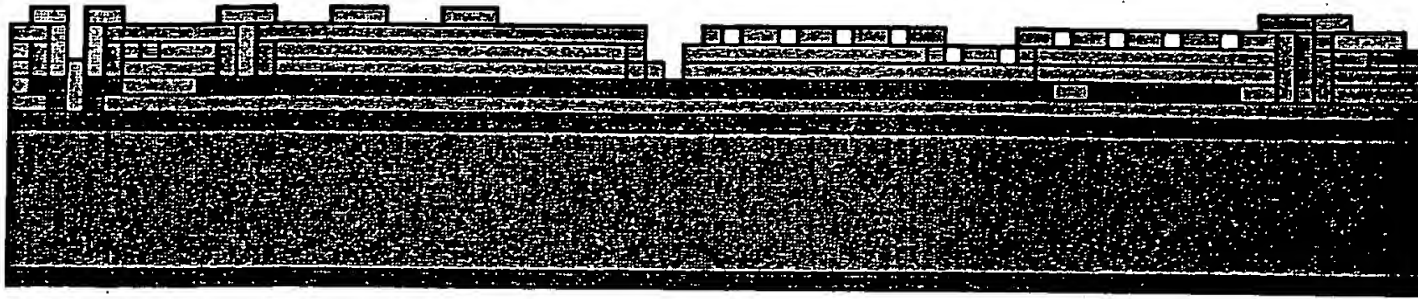


FIG. 4c

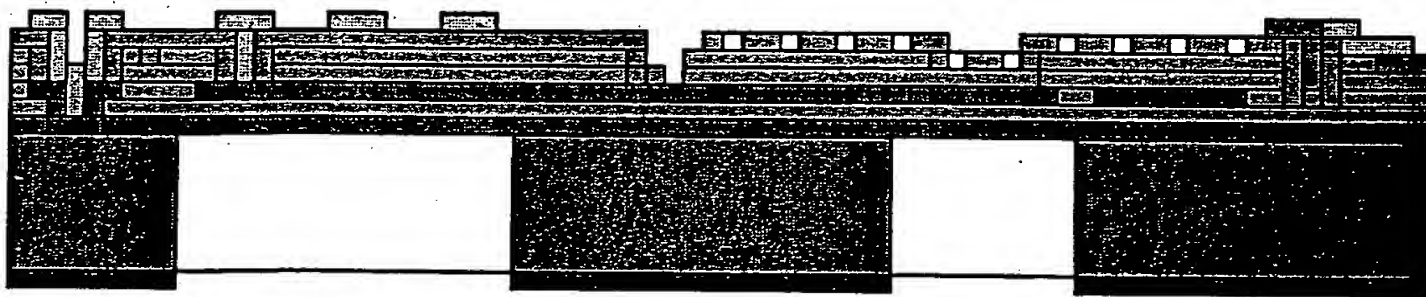




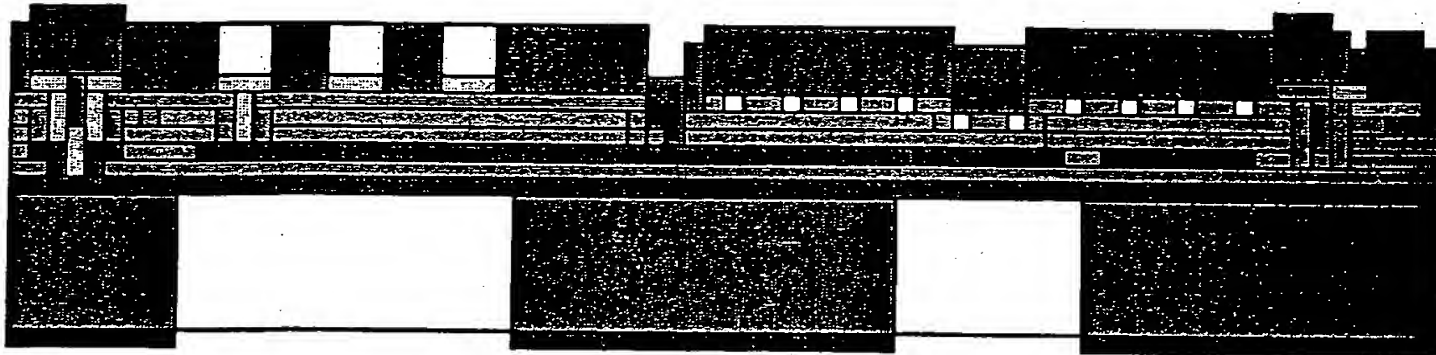
419 Backside stripping (plasma)



420 High aspect ratio ICP etching



421 Electroplating



422 Sacrificial layer wet etching (HF)

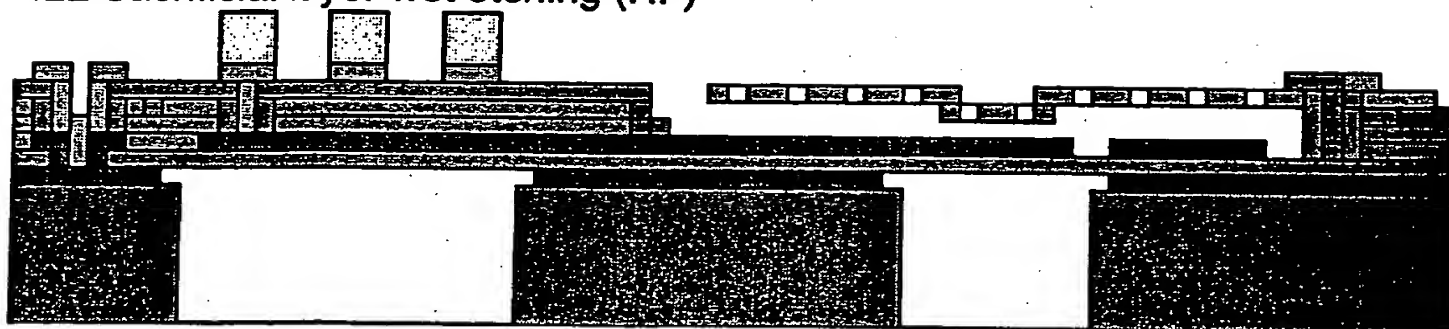
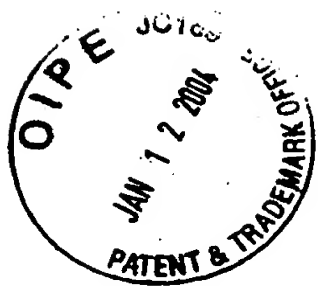


FIG. 4d



500

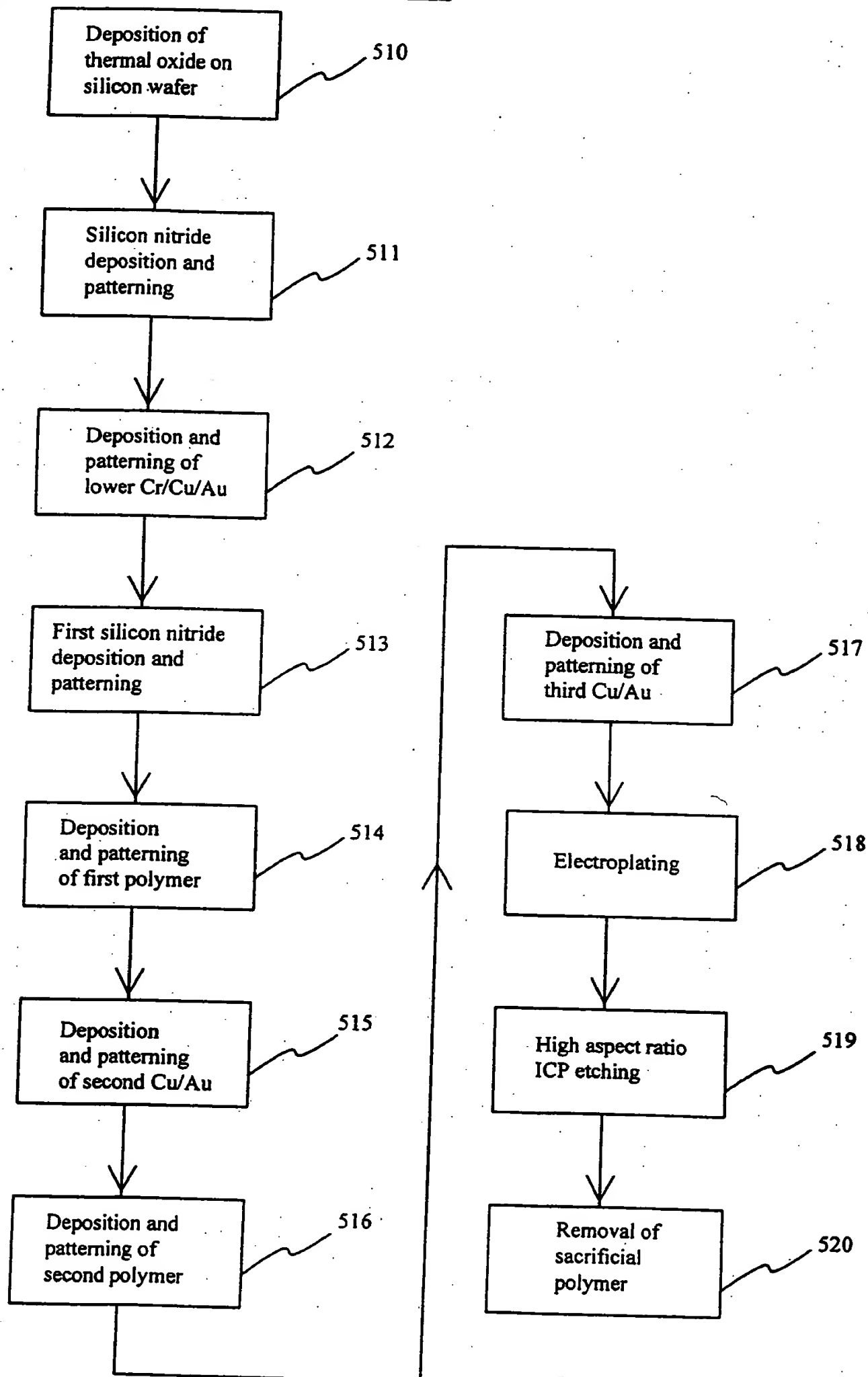
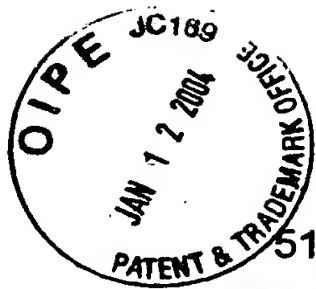
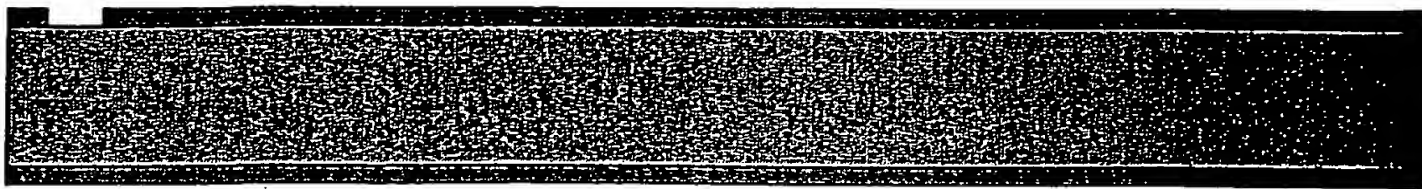


FIG. 5a

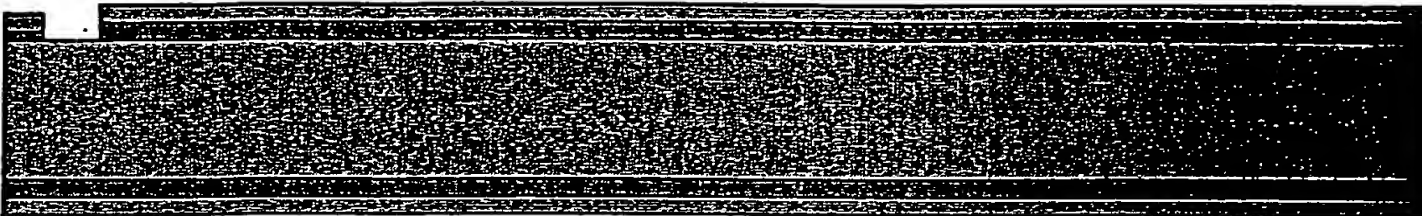




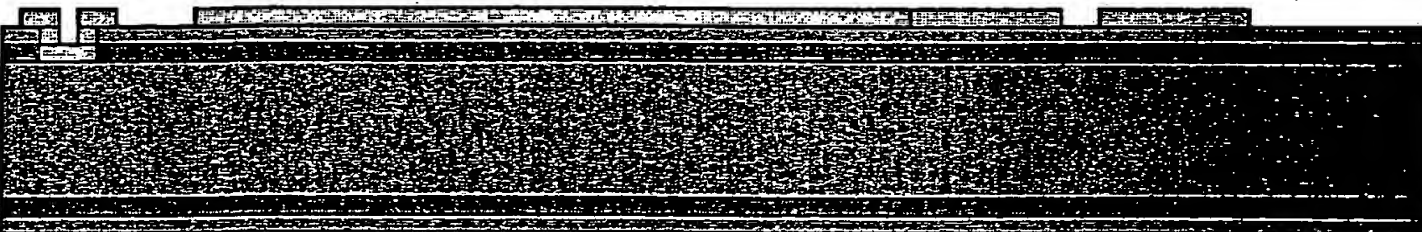
510. Thermal oxide ( $\sim 1\mu\text{m}$ )



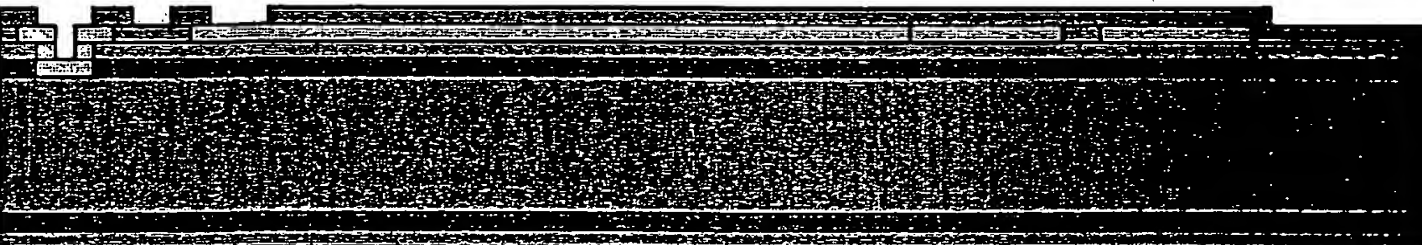
511 Silicon nitride deposition ( $\sim 1\mu\text{m}$ ) and patterning



512 Lower Cr/Cu/Au deposition and patterning



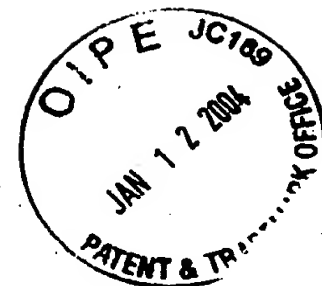
513 Silicon nitride deposition ( $0.2 - 0.3\mu\text{m}$ ) and patterning



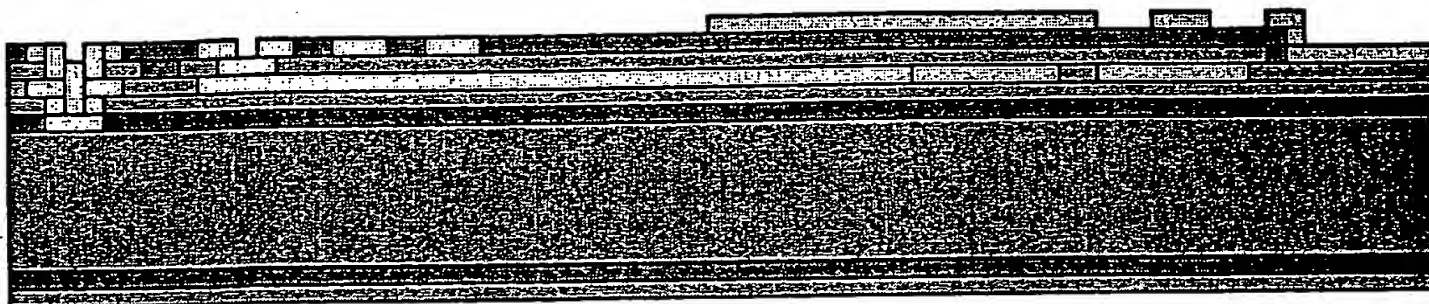
514 First polymer deposition and patterning



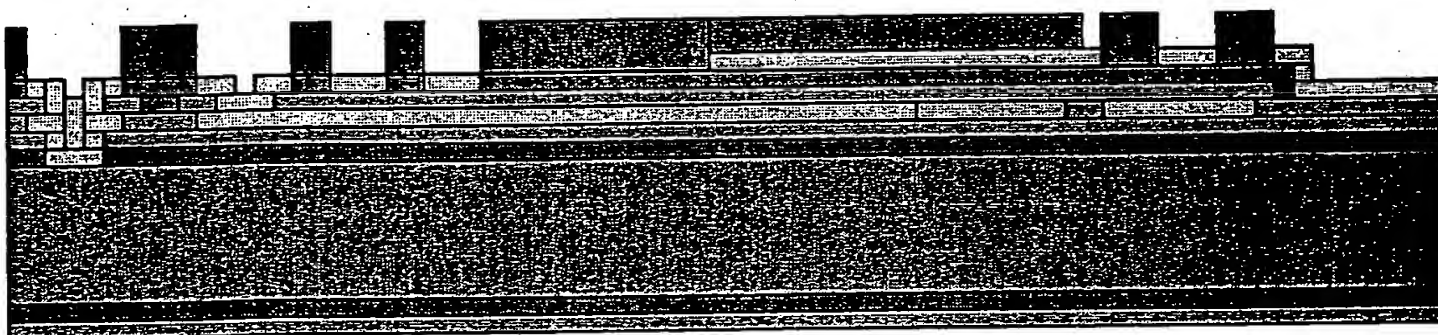
FIG. 5b



515 Second Cu/Au deposition and patterning



516 Second polymer deposition and patterning



517 Third Cu/Au deposition and patterning

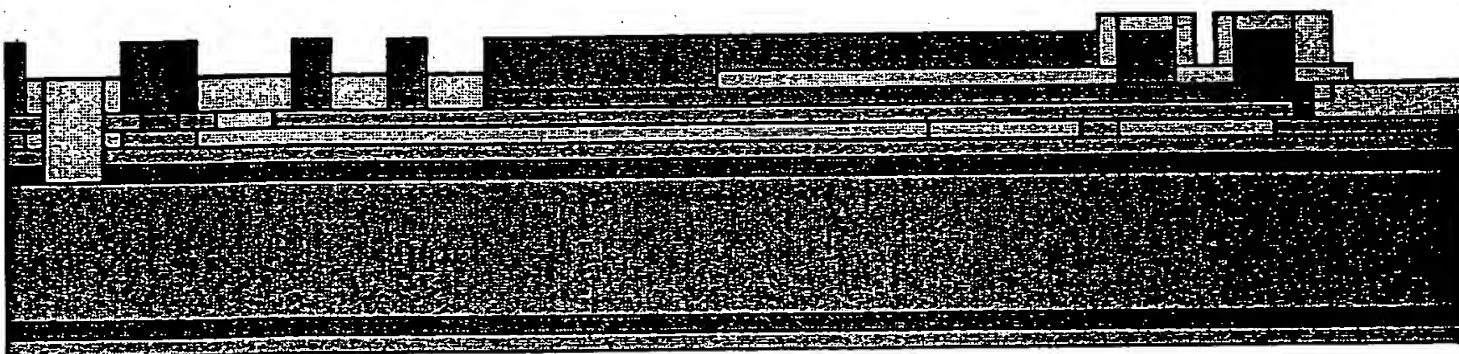
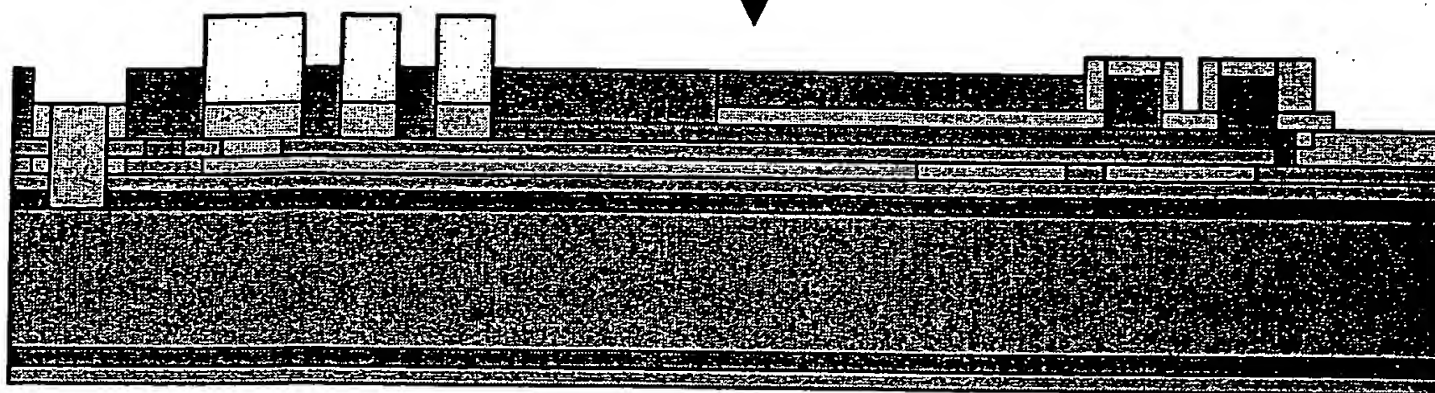


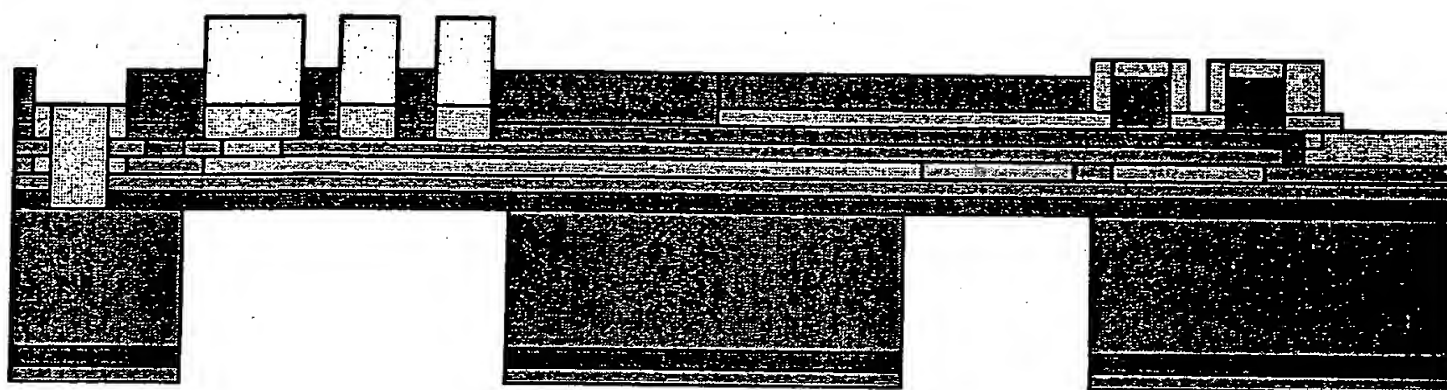
FIG. 5c



518 Electroplating



519 High aspect ratio ICP etching



520 Sacrificial polymer removal

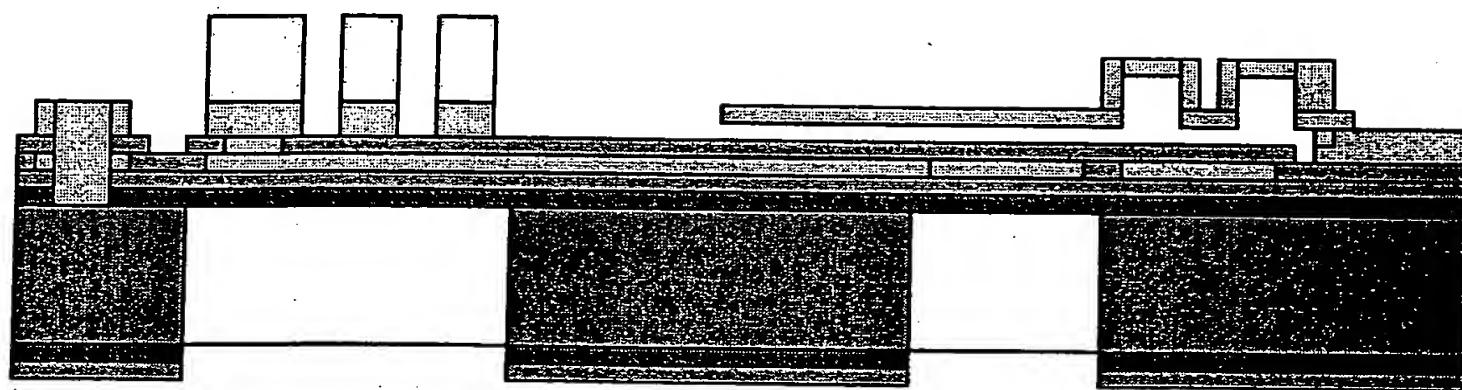


FIG. 5d

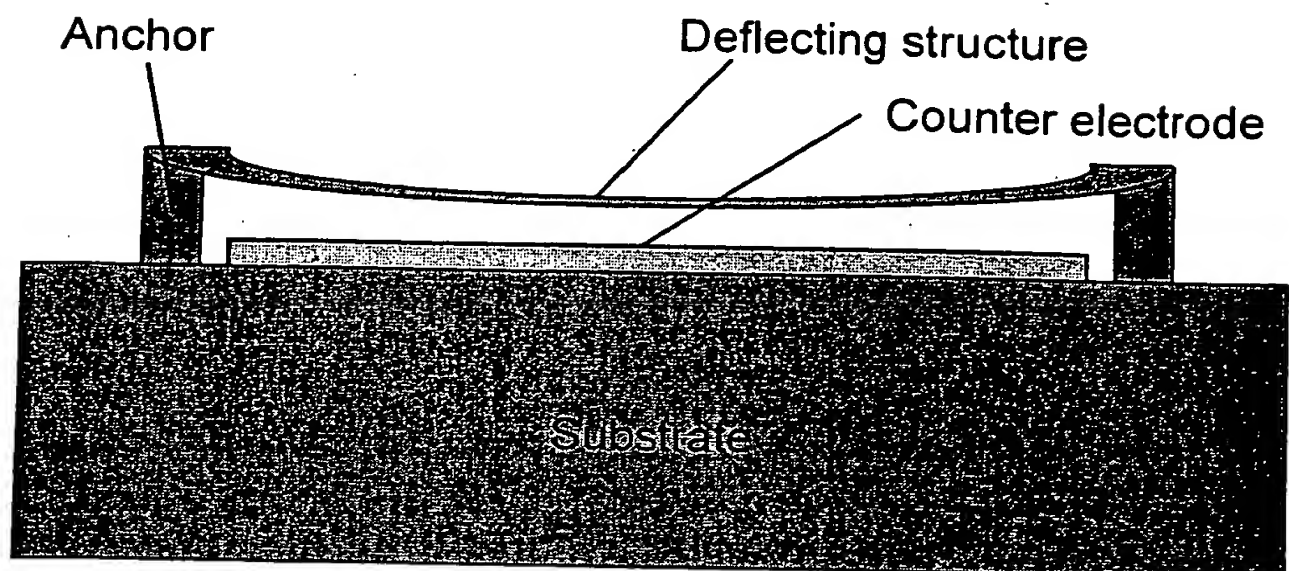
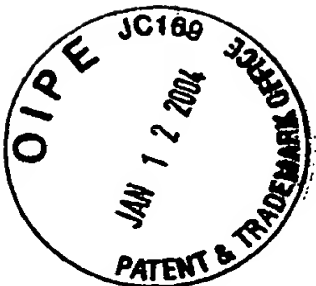


Fig. 6a  
PRIOR ART

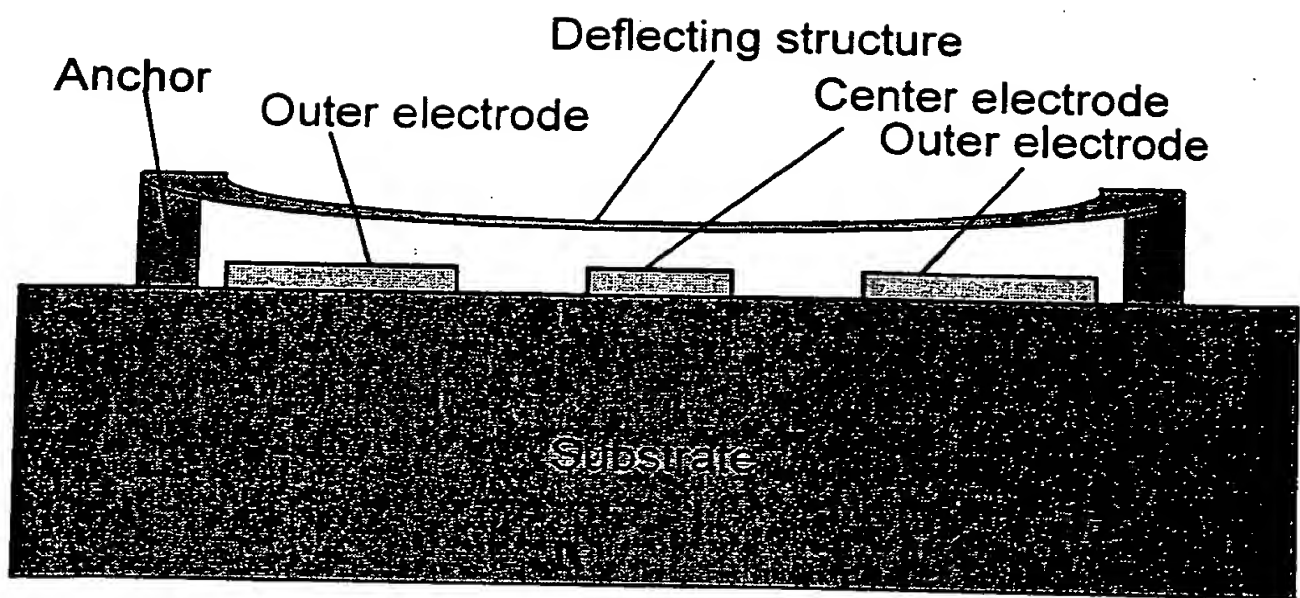


Fig. 6b

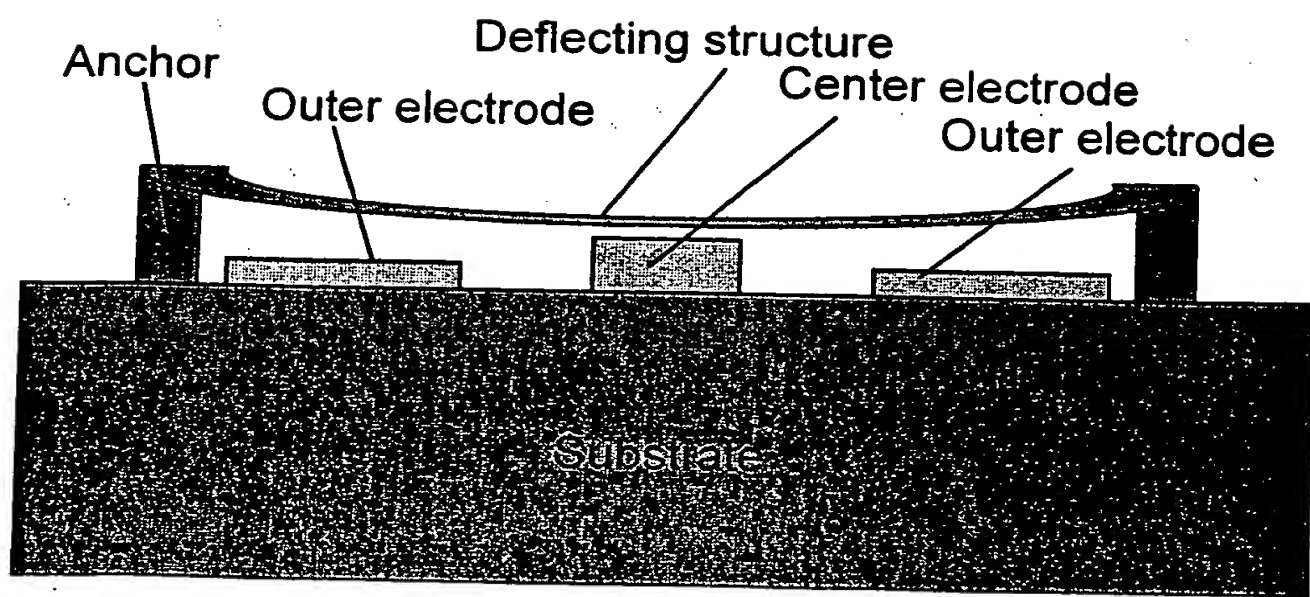


Fig. 6c



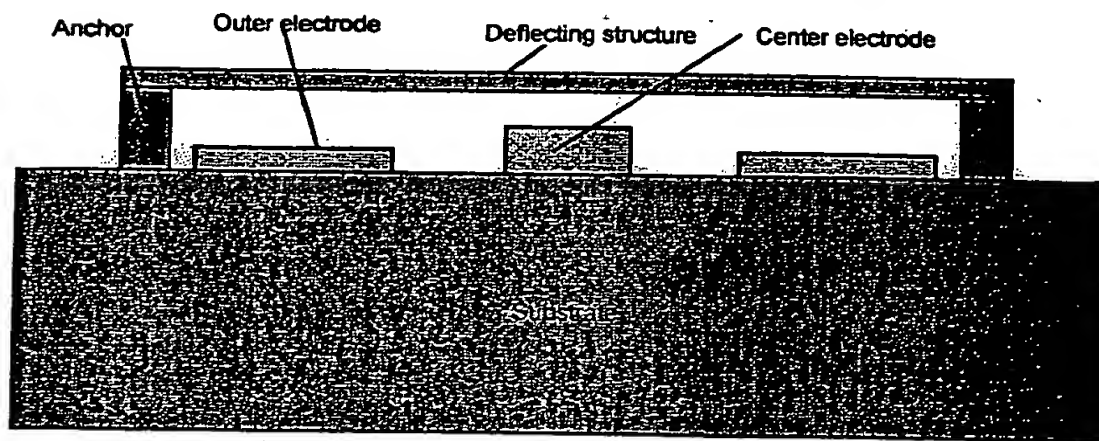
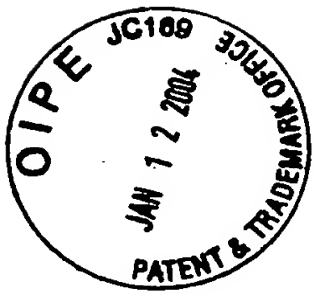


Fig. 7a

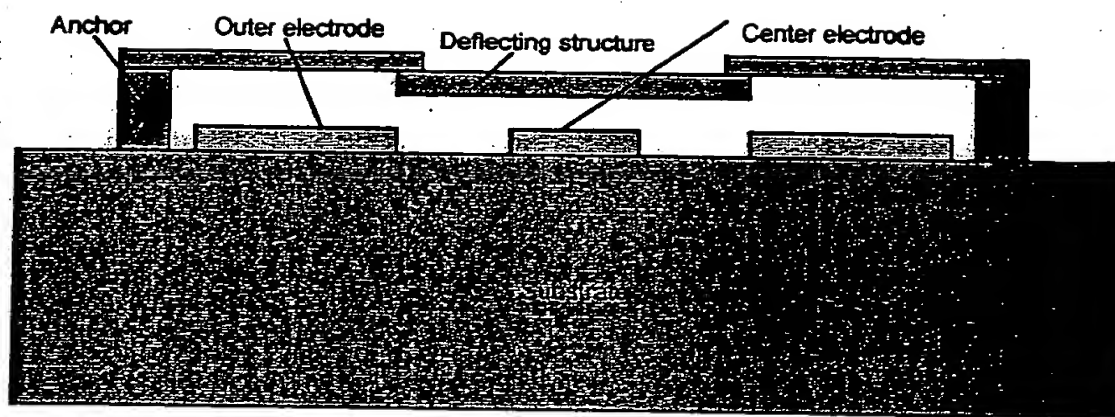


Fig. 7b

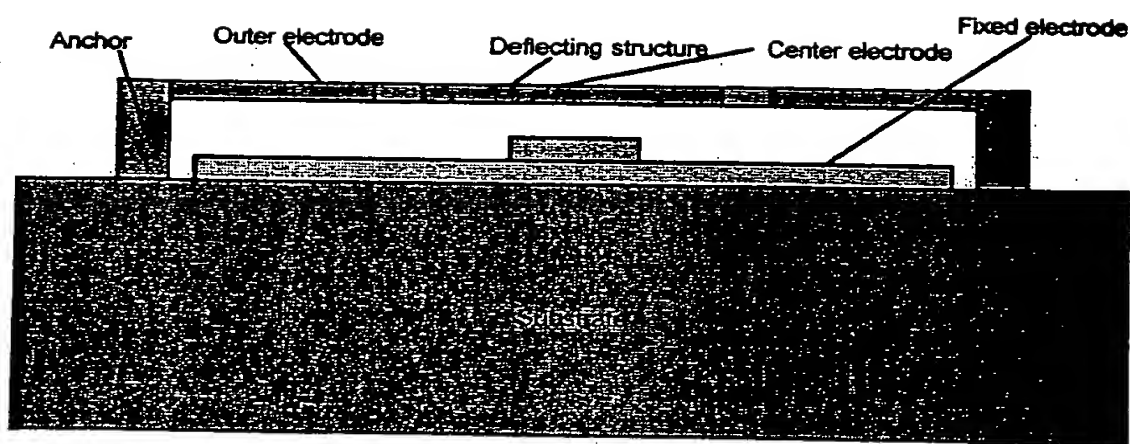


Fig. 7c

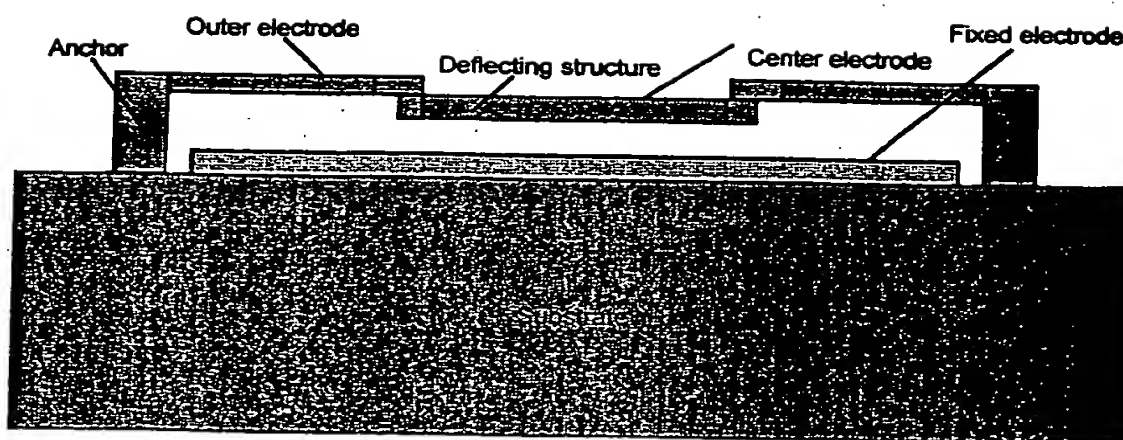


Fig. 7d

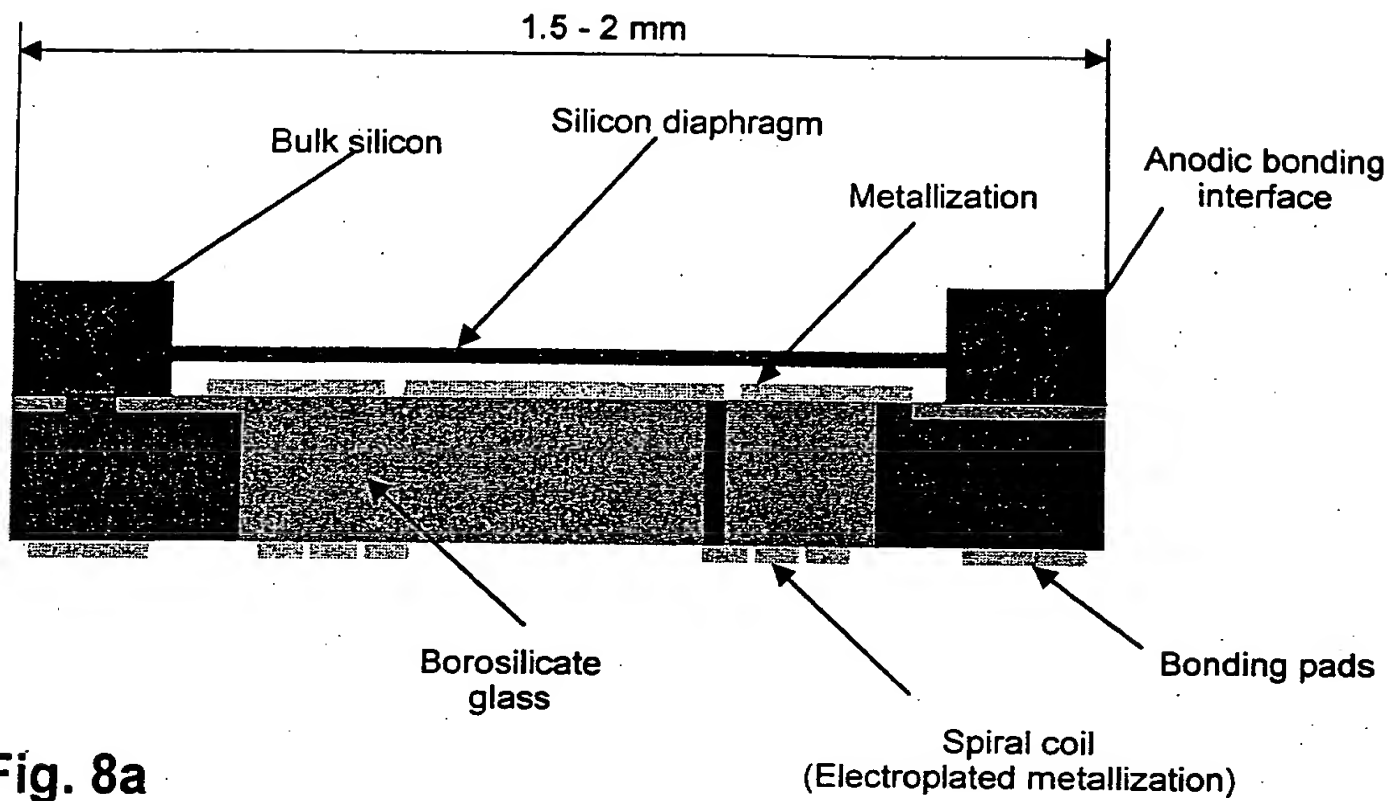
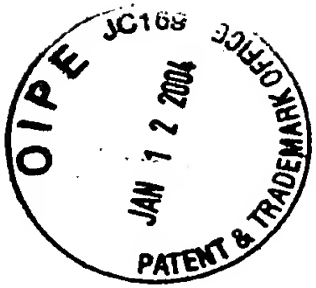


Fig. 8a

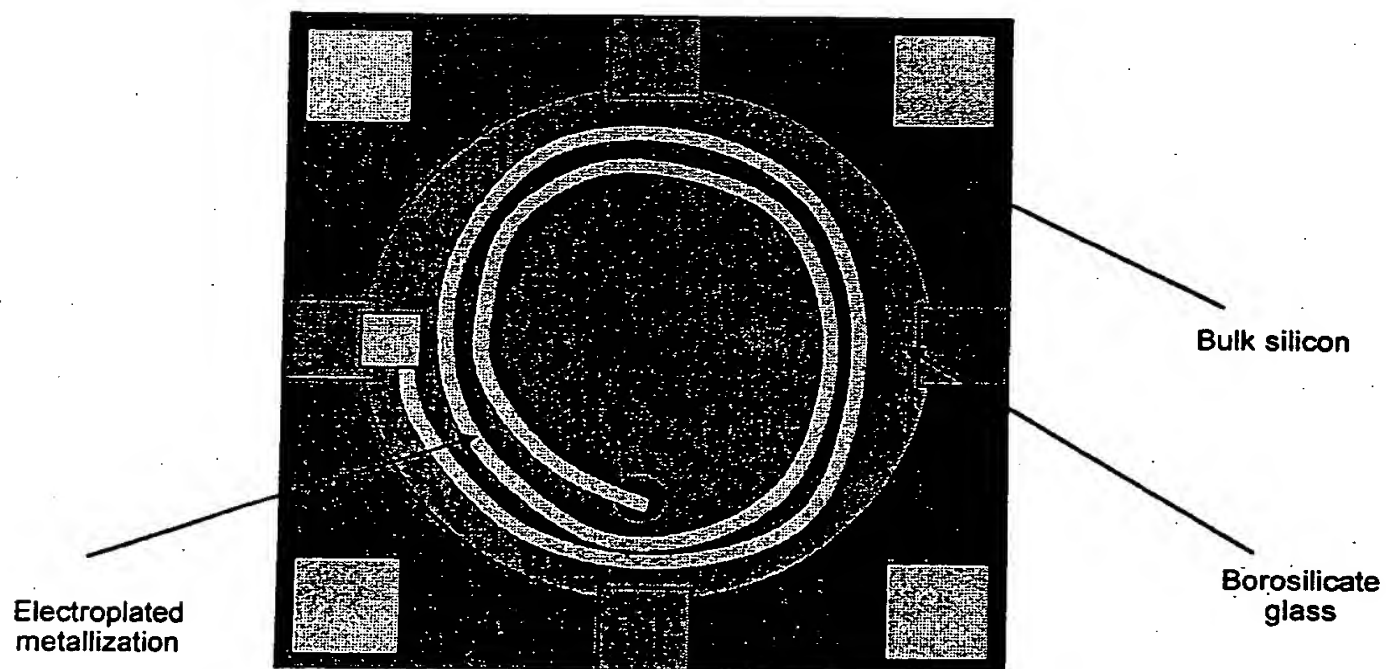


Fig. 8b



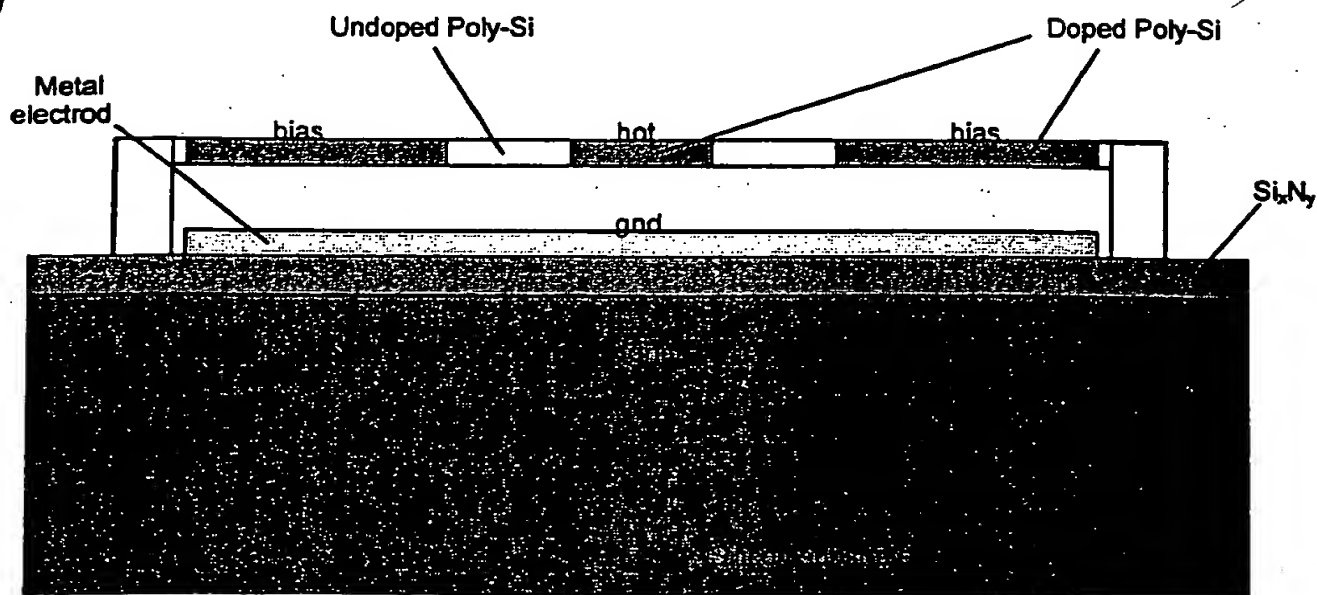


Fig. 9

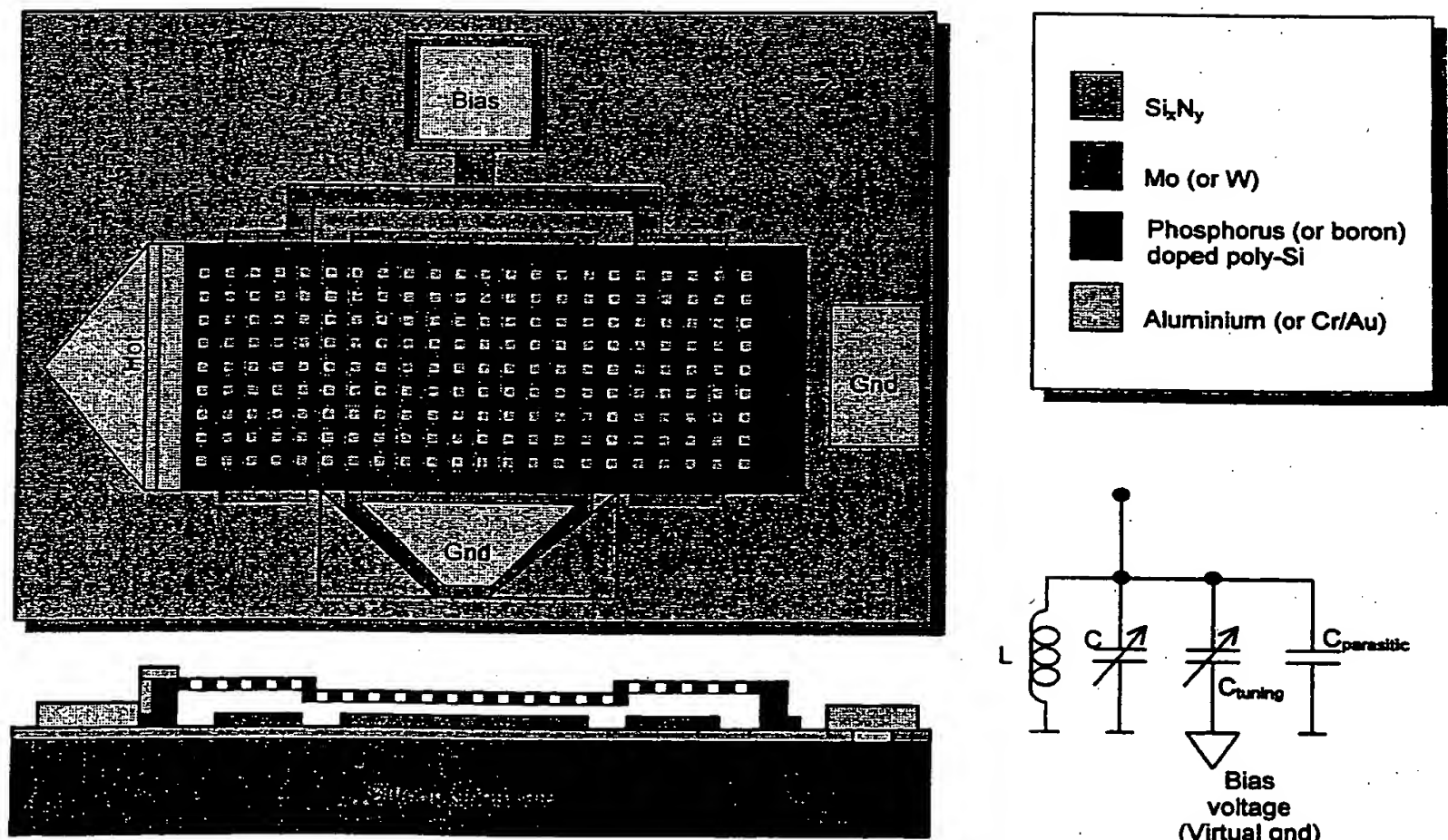


Fig. 10c

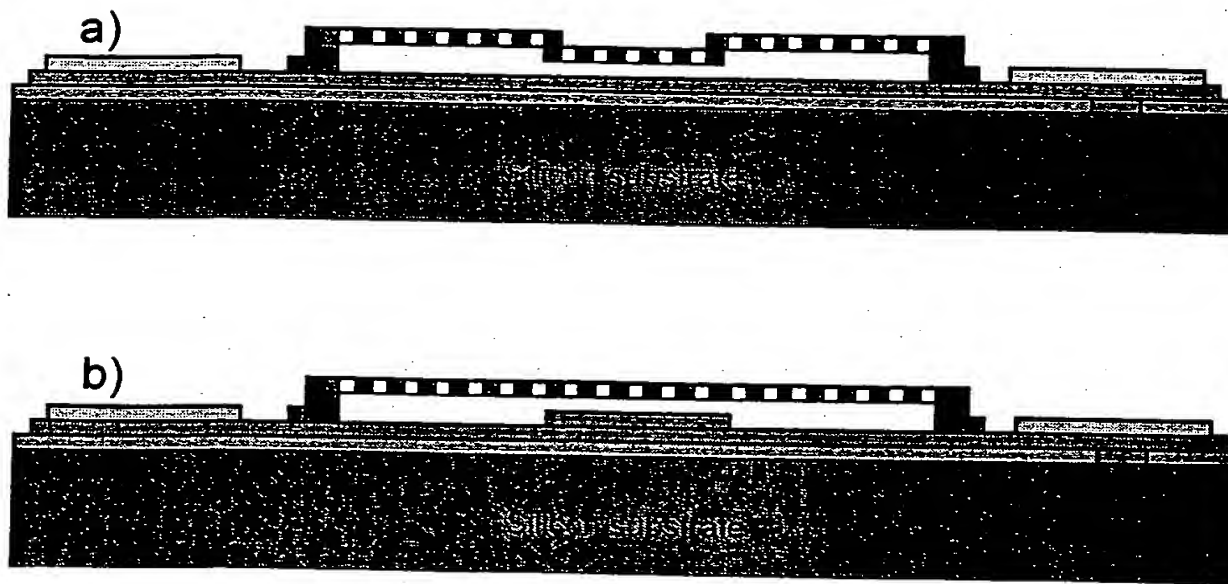
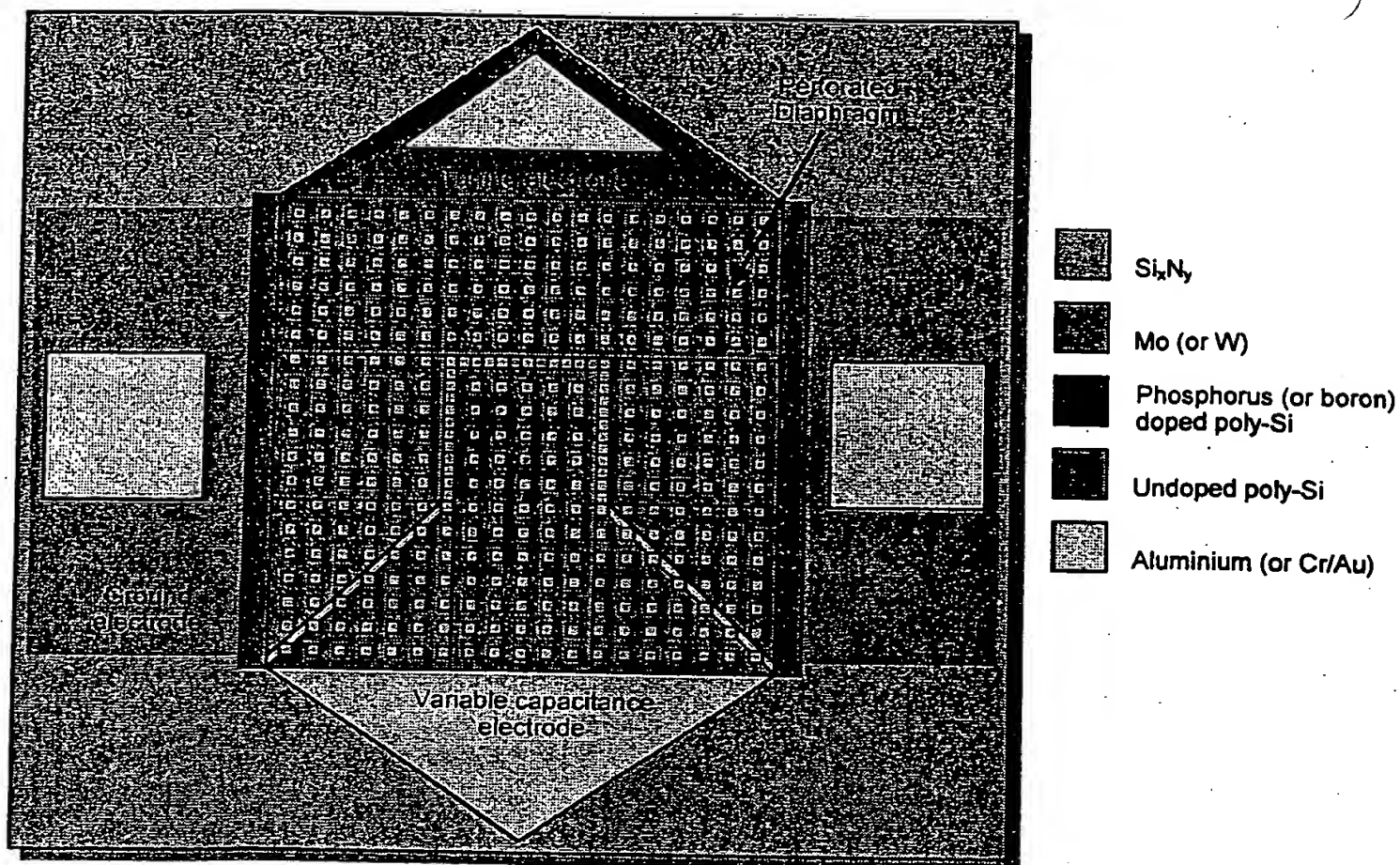
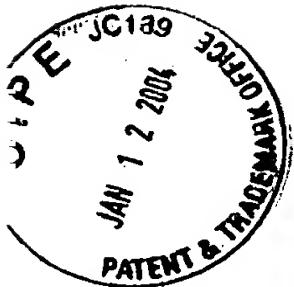


Fig. 10a,b

